ISO7310x 优异电磁兼容性 (EMC) 低功耗单通道数字隔离器

1 特性

- 信号传输速率：25Mbps
- 输入端集成有噪声滤波器
- 默认输出“高电平”和“低电平”选项
- 低功耗：I_{CC} 典型值
  - 1Mbps 时为 1.9mA，25Mbps 时为 3.8mA（5V 电源供电时）
  - 1Mbps 时为 1.4mA，25Mbps 时为 2.6mA（3.3V 电源供电时）
- 低传播延迟：典型值 32ns（5V 电源供电时）
- 3.3V 和 5V 电平转换
- 宽 T_A 额定范围：-40°C 至 125°C
- 65KV/μs 瞬态抗扰度，典型值（5V 电源供电时）
- 优异的电磁兼容性 (EMC)
  - 系统级静电放电 (ESD)、瞬态放电 (EFT) 以及抗浪涌保护
  - 低辐射
- 隔离隔栅寿命：> 25 年
- 可由 3.3V 和 5V 电压供电
- 窄体小尺寸集成电路 (SOIC)-8 封装
- 安全及管理批准:
  - 符合 DIN V VDE V 0884-10 标准和 DIN EN 61010-1 标准的 4242 V_{PK} 隔离 ”中）中）
  - 符合 UL 1577 标准且长达 1 分钟的 3000 V_{RMS} 隔离”
  - CSA 组件接受通知 5A，IEC 60950-1 和 IEC 61010-1 终端设备标准中的 CSA 组件接受列表项中 CSA 组件接受列表项的“（审批正在审理中）”
  - 符合 GB4943.1-2011 的 CQC 认证的“所有机构的审批已通过”

2 应用

- 在下列应用中的光电耦合器替代产品：
  - 工业用 FieldBus
    - ProfiBus
    - ModBus
    - DeviceNet™ 数据总线
  - 伺服控制接口
  - 电机控制
  - 电源
  - 电池组

3 说明

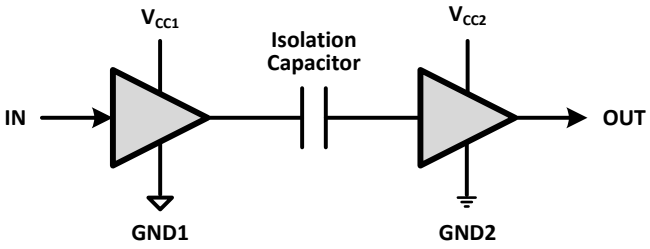
ISO7310x 可提供符合 UL 标准的长达 1 分钟且高达 3000 V_{RMS} 的电流隔离，以及符合 VDE 标准的 4242 V_{PK} 隔离。 这些器件具有一个隔离通道，其逻辑输入和输出缓冲器由二氧化硅 (SiO_2) 绝缘隔栅分离开来。 通过与隔离电源一起使用，ISO7310x 可防止数据总线或者其它电路上的噪声电流进入本地接地端并干扰或者损坏敏感电路。 这些器件已针对恶劣环境集成了噪声滤波器，在此类环境下，器件的输入引脚上可能会出现短噪音脉冲。 ISO7310x 具有晶体管晶体管逻辑电路 (TTL) 输入阈值，工作电压范围为 3V 到 5.5V。 凭借创新的芯片设计和布线技术，ISO7310x 的电磁兼容性得到了显著增强，从而可确保提供系统级 ESD、EFT 和浪涌保护并符合辐射标准。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
ISO7310C	SOIC (8)	4.90mm x 3.91mm
ISO7310FC		

(1) 如需了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

目录

4 修订历史记录

Changes from Revision C (March 2015) to Revision D **Page**

- 已添加“和 DINEN 61010-1 标准”至“4242 V_{PK}”（*特性* ... 1
- 已删除*特性* ... 1
- Deleted IEC from the section title: *Insulation and Safety-Related Specifications for D-8 Package* ... 12
- Changed the CTI Test Conditions in *Insulation and Safety-Related Specifications for D-8 Package* ... 12
- Changed V_{ISO} Test Condition in the *Insulation Characteristics* table ... 13
- Changed column CSA in the *Regulatory Information* table ... 13

Changes from Revision B (September 2014) to Revision C **Page**

- 已将*特性*中的“输入引脚上集成有噪声滤波器”更改为“输入端集成有噪声滤波器” ... 1
- 已添加*特性* - 默认输出“高电平”和“低电平”选项 ... 1
- 已将“DIN V VDE 0884-10 标准”更改为 “DIN V VDE V 0884-10”（*特性* ... 1
- 已将*特性*中的“3 KV_{RMS} 隔离”更改为“3000 V_{RMS} 隔离 ... 1
- 已添加“（审批正在审理中）”至*特性* ... 1
- 已将*特性*中的“通过 GB4943.1-2011 CQC 认证”更改为“符合 GB4943.1-2011 的 CQC 认证” ... 1
- 已将*简化电路原理图*中的 GND1 更改为 GNDI，GND2 更改为 GNDO ... 1
- Changed the *Handling Ratings* to *ESD Ratings* table and updated guidelines ... 5
- Changed the CTI MIN value in *Insulation and Safety-Related Specifications for D-8 Package* From: >400 V To: 400 V .. 12
- Added "DT1" to the Minimum internal gap in *Insulation and Safety-Related Specifications for D-8 Package* ... 12
- Changed the DTI MIN value in *Insulation and Safety-Related Specifications for D-8 Package* From: 0.014 mm To: 13 µM ... 12
- Changed the R_{IO} Test Condition in *Insulation and Safety-Related Specifications for D-8 Package* From: T_A < 100°C To: T_A = 25°C ... 12
- Changed the R_{IO} Test Condition in *Insulation and Safety-Related Specifications for D-8 Package* From: T_A ≤ max To: T_A = 125°C ... 12
- Changed DIN V VDE 0884-10 To: DIN V VDE V 0884-10 in the *Insulation Characteristics* ... 13
- Added V_{IOSM} to the *Insulation Characteristics* table ... 13

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- Changed R_S Test Conditions in *Insulation Characteristics* From: T_S To: T_S = 150°C 13
- Changed the *Regulatory Information* table, VDE Certified From: DIN V VDE 0884-10 To: DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 61010-1 (VDE 0411-1):2011-07 13
- Changed the *Regulatory Information* table, deleted (Approval Pending) statement 13
- Changed the *Regulatory Information* table, CQC Certified number From: CQC14001109540 To: CQC15001121656 13
- Changed title From: " IEC Safety Limiting Values" To: Safety Limiting Values 14
- Changed Table 2 Header information to include device number for the OUT column. Added Note 3. 15
- Changed Figure 14 to include a diode at V_{CC1} on the Input circuit 15
- Changed Figure 15 16
- Added Figure 16 17

Changes from Revision A (July 2014) to Revision B **Page**

- 添加了器件 ISO7310FC 1
- 已将特性中的 “符合 DIN EN 60747-5-5 (VDE 0884-5) 标准的 4242 V_{PK} 隔离”更改为 “符合 DIN V VDE 0884-10 标准的 4242 V_{PK} 隔离 1
- 已删除*特性*安全及管理批准 1
- Replaced Figure 10 10
- Changed DIN EN 60747-5-5 To: DIN V VDE 0884-10 in the *Insulation Characteristics* 13
- Changed DIN EN 60747-5-5 (VDE 0884-5) To: DIN V VDE 0884-10 in the *Regulatory Information* table 13
- Added a NOTE in the Application Information section 16

Changes from Original (March 2014) to Revision A **Page**

- 从单页产品预览更改为完整数据表 1
- 已添加*特性* - 通过 GB4943.1-2011 CQC 认证 1
- 更改了说明部分，新增：“凭借创新的芯片设计...” 1
- 已更改*简化电路原理图* 1

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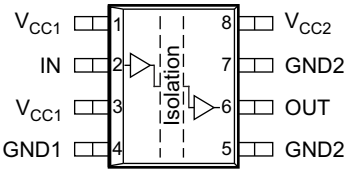
5 Pin Configuration and Functions

D PACKAGE
(TOP VIEW)



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NUMBER		
V_{CC1}	1, 3	–	Power supply, V_{CC1}
IN	2	I	Input
GND1	4	–	Ground connection for V_{CC1}
GND2	5, 7	–	Ground connection for V_{CC2}
OUT	6	O	Output
V_{CC2}	8	–	Power supply, V_{CC2}

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6 Specifications

6.1 Absolute Maximum Ratings(1)

		MIN	MAX	UNIT
Supply voltage(2)	V_{CC1} , V_{CC2}	–0.5	6	V
Voltage (2)	IN, OUT	–0.5	V_{CC}+0.5(3)	V
Output current	I_O		±15	mA
Junction temperature	T_J		150	°C
Storage temperature	T_{stg}	–65	150	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal and are peak voltage values.
(3) Maximum voltage must not exceed 6 V.

6.2 ESD Ratings

			MAX	UNIT
V_{ESD}	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	TYP	MAX	UNIT
V_{CC1}, V_{CC2}	Supply voltage	3		5.5	V
I_{OH}	High-level output current	–4			mA
I_{OL}	Low-level output current			4	mA
V_{IH}	High-level input voltage	2		5.5	V
V_{IL}	Low-level input voltage	0		0.8	V
t_{ui}	Input pulse duration	40			ns
1 / t_{ui}	Signaling rate	0		25	Mbps
T_J (1)	Junction temperature			136	°C
T_A	Ambient temperature	-40	25	125	°C

(1) To maintain the recommended operating conditions for T_J, see the *Thermal Information* table.

6.4 Thermal Information

THERMAL METRIC(1)			D PACKAGE (8) PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance		119.9	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance		65.2	
$R_{\theta JB}$	Junction-to-board thermal resistance		61.3	
ψ_{JT}	Junction-to-top characterization parameter		19.3	
ψ_{JB}	Junction-to-board characterization parameter		60.7	
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance		N/A	
P_D	Maximum power dissipation	V_{CC1} = V_{CC2} = 5.5 V, T_J = 150°C, C_L = 15 pF, Input a 12.5 MHz 50% duty-cycle square wave	34	mW
P_{D1}	Power dissipation by Side-1		7.9	
P_{D2}	Power dissipation by Side-2		26.1	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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6.5 Electrical Characteristics

V_{CC1} and V_{CC2} at 5 V ± 10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 9		V_{CC2} – 0.5	4.7		V
		I_{OH} = –20 µA; see Figure 9		V_{CC2} – 0.1	5		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 9			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 9			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				480		mV
I_{IH}	High-level input current	IN = V_{CC}				10	µA
I_{IL}	Low-level input current	IN = 0 V		–10			µA
CMTI	Common-mode transient immunity	V_I = V_{CC} or 0 V; see Figure 11.		25	65		kV/µs
SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic I_{CC} measurement)							
I_{CC1}	Supply current for V_{CC1} and V_{CC2}	DC to 1 Mbps	DC Input: V_I = V_{CC} or 0 V, AC Input: C_L = 15pF		0.3	0.6	mA
I_{CC2}					1.6	2.4	
I_{CC1}		10 Mbps	C_L = 15pF		0.5	1	
I_{CC2}					2.2	3.2	
I_{CC1}		25 Mbps	C_L = 15pF		0.8	1.3	
I_{CC2}					3	4.2	

6.6 Switching Characteristics

V_{CC1} and V_{CC2} at 5 V ± 10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 9	20	32	58	ns
PWD (1)	Pulse width distortion $\lvert t_{PHL} - t_{PLH} \rvert$				4	ns
$t_{sk(pp)}$ (2)	Part-to-part skew time				24	ns
t_r	Output signal rise time	See Figure 9		2.5		ns
t_f	Output signal fall time			2		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 10		7.5		µs

(1) Also known as pulse skew.
(2) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

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6.7 Electrical Characteristics

V_{CC1} and V_{CC2} at 3.3 V ± 10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 9		V_{CC2} – 0.5	3		V
		I_{OH} = –20 µA; see Figure 9		V_{CC2} – 0.1	3.3		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 9			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 9			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				450		mV
I_{IH}	High-level input current	IN = V_{CC}				10	µA
I_{IL}	Low-level input curre	IN = 0 V		-10			µA
CMTI	Common-mode transient immunity	V_I = V_{CC} or 0 V; see Figure 11		25	50		kV/µs
SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic I_{CC} measurement)							
I_{CC1}	Supply current for V_{CC1} and V_{CC2}	DC to 1 Mbps	DC Input: V_I = V_{CC} or 0 V, AC Input: C_L = 15pF		0.2	0.4	mA
I_{CC2}					1.2	1.8	
I_{CC1}		10 Mbps	C_L = 15pF		0.3	0.5	
I_{CC2}					1.6	2.2	
I_{CC1}		25 Mbps	C_L = 15pF		0.5	0.8	
I_{CC2}					2.1	3	

6.8 Switching Characteristics

V_{CC1} and V_{CC2} at 3.3 V ± 10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 9	22	36	67	ns
PWD (1)	Pulse width distortion $\lvert t_{PHL} - t_{PLH} \rvert$				3.5	ns
$t_{sk(pp)}$ (2)	Part-to-part skew time				28	ns
t_r	Output signal rise time	See Figure 9		3.2		ns
t_f	Output signal fall time			2.7		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 10		7.4		µs

(1) Also known as pulse skew.
(2) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

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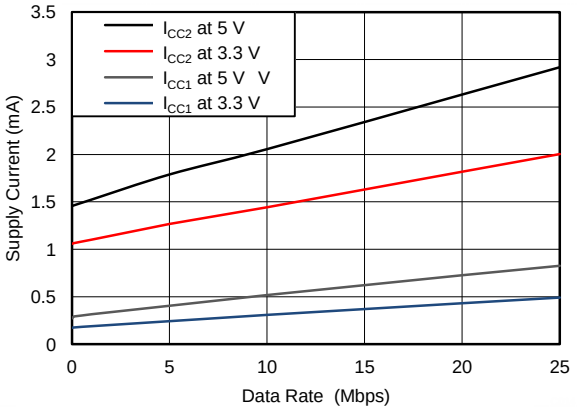
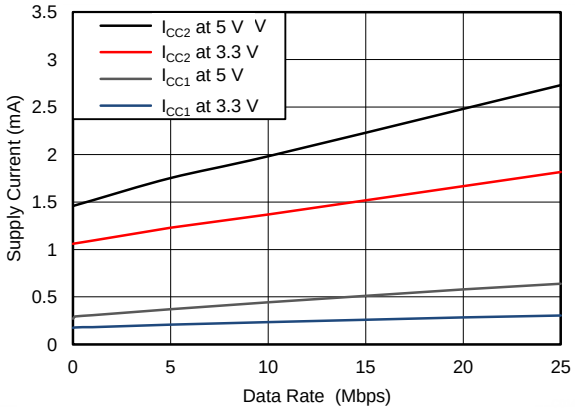
6.9 Typical Characteristics



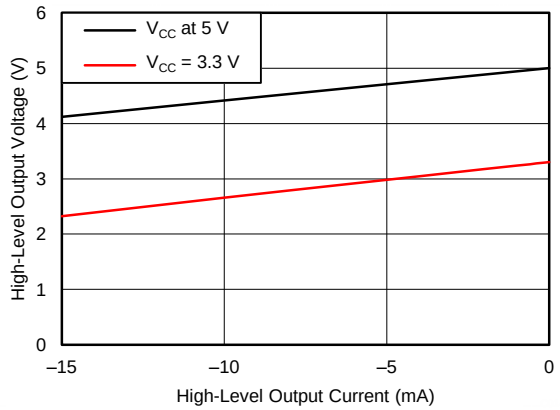
T_A = 25°C C_L = 15 pF

Figure 1. Supply Current vs Data Rate (with 15 pF Load)



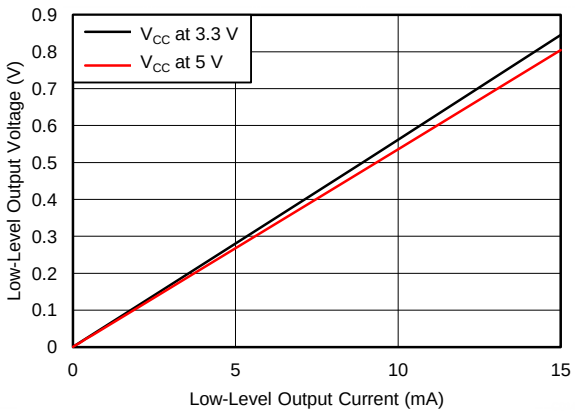
T_A = 25°C C_L = No Load

Figure 2. Supply Current vs Data Rate (with No Load)



T_A = 25°C

Figure 3. High-Level Output Voltage vs High-level Output Current



T_A = 25°C

Figure 4. Low-Level Output Voltage vs Low-Level Output Current

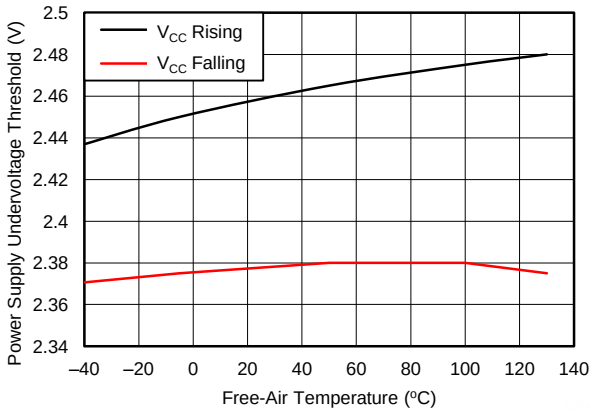


Figure 5. Power Supply Undervoltage Threshold vs Free-Air Temperature

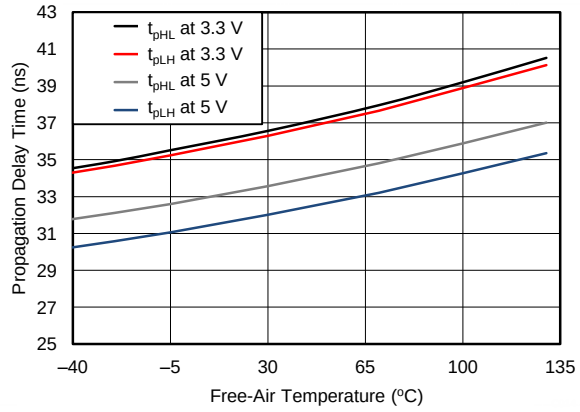


Figure 6. Propagation Delay Time vs Free-Air Temperature

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Typical Characteristics (continued)

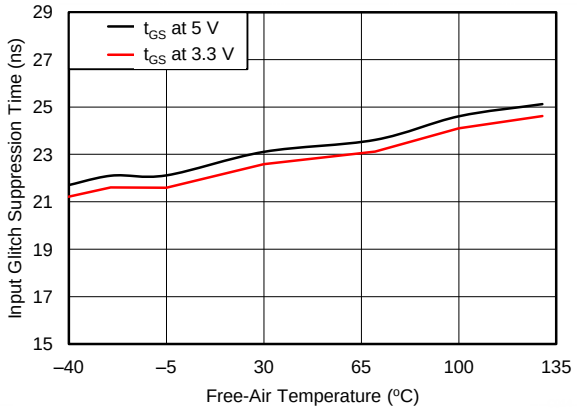


Figure 7. Input Glitch Suppression Time vs Free-Air Temperature

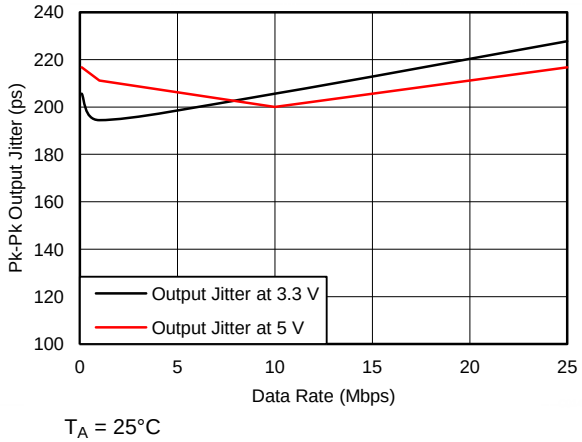
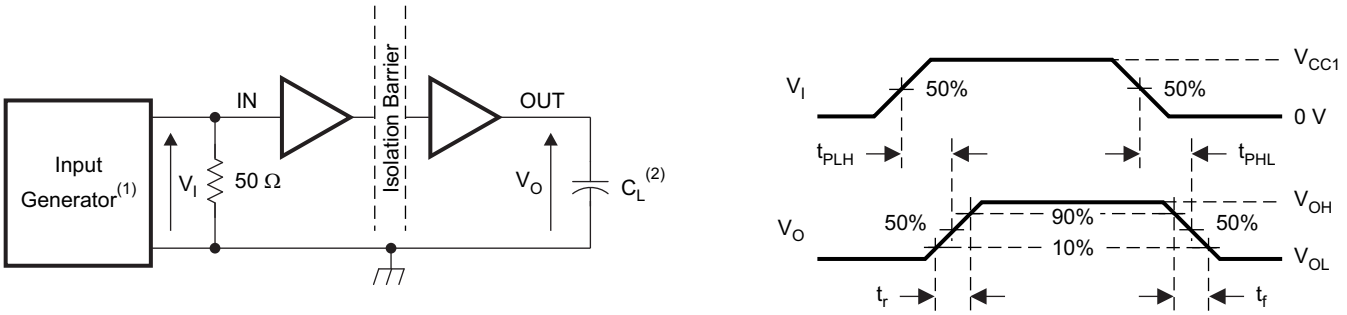


Figure 8. Output Jitter vs Data Rate

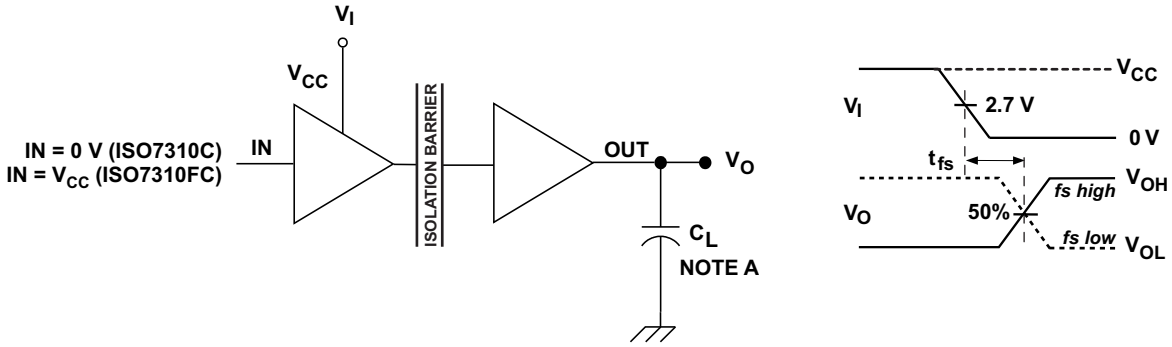
7 Parameter Measurement Information



(1) The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50 Ω. At the input, a 50-Ω resistor is required to terminate the Input Generator signal. It is not needed in actual application.

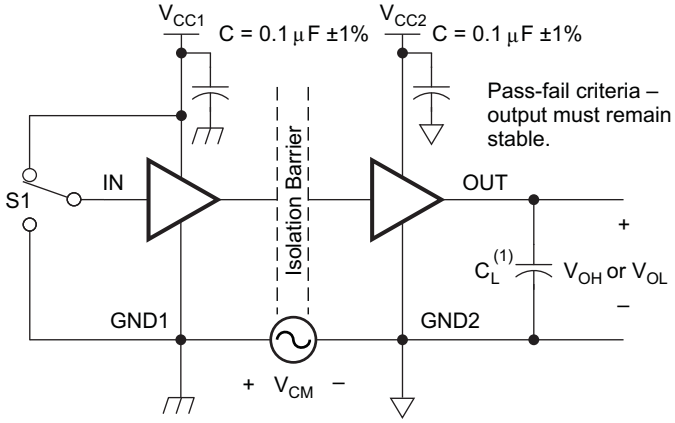
(2) C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 9. Switching Characteristic Test Circuit and Voltage Waveforms



A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 10. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



(1) C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 11. Common-Mode Transient Immunity Test Circuit

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8 Detailed Description

8.1 Overview

The isolator in Figure 12 is based on a capacitive isolation barrier technique. The I/O channel of the device consists of two internal data channels, a high-frequency (HF) channel with a bandwidth from 100 kbps up to 25 Mbps, and a low-frequency (LF) channel covering the range from 100 kbps down to DC.

In principle, a single-ended input signal entering the HF channel is split into a differential signal via the inverter gate at the input. The following capacitor-resistor networks differentiate the signal into transient pulses, which then are converted into CMOS levels by a comparator. The transient pulses at the input of the comparator can be either above or below the common mode voltage VREF depending on whether the input bit transitioned from 0 to 1 or 1 to 0. The comparator threshold is adjusted based on the expected bit transition. A decision logic (DCL) at the output of the HF channel comparator measures the durations between signal transients. If the duration between two consecutive transients exceeds a certain time limit, (as in the case of a low-frequency signal), the DCL forces the output-multiplexer to switch from the high-frequency to the low-frequency channel.

8.2 Functional Block Diagram

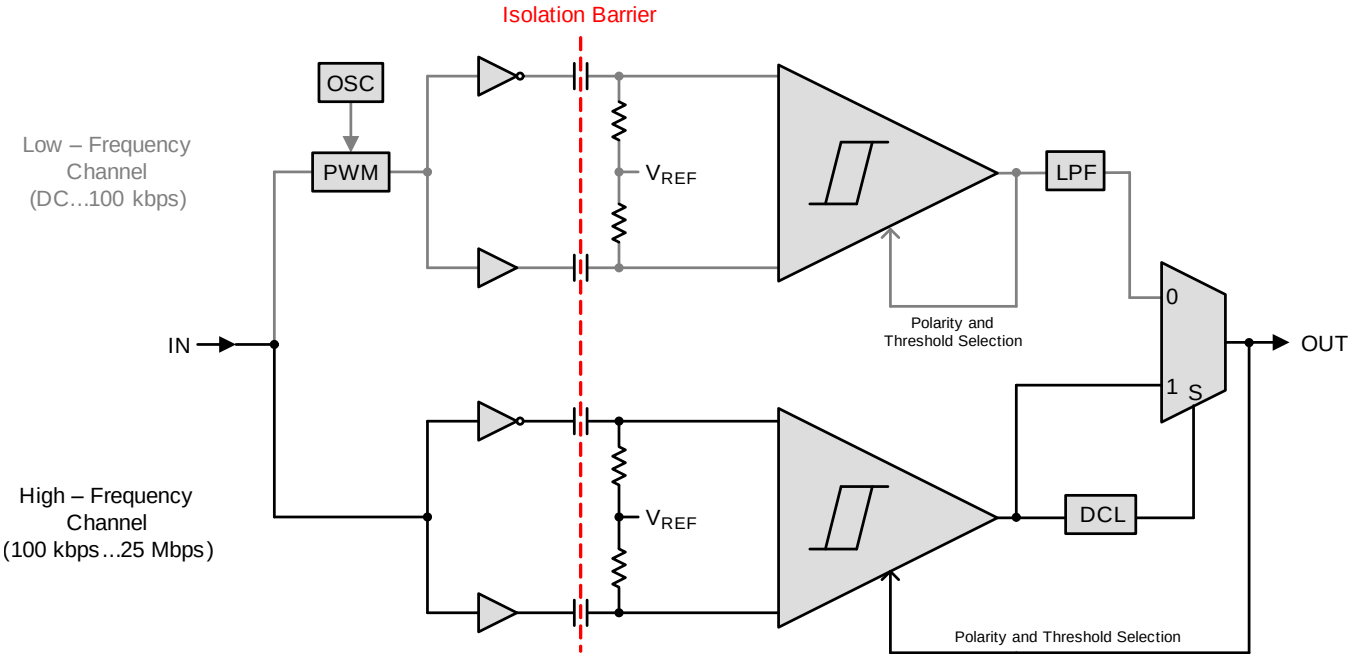

Figure 12. Conceptual Block Diagram of a Digital Capacitive Isolator

Because low-frequency input signals require the internal capacitors to assume prohibitively large values, these signals are pulse-width modulated (PWM) with the carrier frequency of an internal oscillator, thus creating a sufficiently high frequency, capable of passing the capacitive barrier. As the input is modulated, a low-pass filter (LPF) is needed to remove the high-frequency carrier from the actual data before passing it on to the output multiplexer.

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8.3 Feature Description

PRODUCT	RATED ISOLATION	MAX DATA RATE	DEFAULT OUTPUT
ISO7310C	3000 V_{RMS} / 4242 V_{PK} (1)	25 Mbps	High
ISO7310FC			Low

(1) See the *Regulatory Information* section for detailed Isolation Ratings

8.3.1 High Voltage Feature Description

8.3.1.1 Insulation and Safety-Related Specifications for D-8 Package

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4			mm
L(I02)	Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4			mm
CTI	Tracking resistance (comparative tracking index)	DIN EN 60112 (VDE 0303-11); IEC 60112	400			V
DTI	Minimum internal gap (internal clearance)	Distance through the insulation	13			µm
R_{IO}	Isolation resistance, input to output(1)	V_{IO} = 500 V, T_A = 25°C		>10^{12}		Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ 125°C		>10^{11}		Ω
C_{IO}	Isolation capacitance, input to output(1)	V_{IO} = 0.4 sin (2πft), f = 1 MHz		0.5		pF
C_I	Input capacitance(2)	V_I = V_{CC}/2 + 0.4 sin (2πft), f = 1 MHz, V_{CC} = 5 V		1.6		pF

(1) All pins on each side of the barrier tied together creating a two-terminal device.
(2) Measured from input pin to ground.

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

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8.3.1.2 Insulation Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER(1)		TEST CONDITIONS	SPECIFICATION	UNIT
V_{IOWM}	Maximum isolation working voltage		400	V_{RMS}
V_{IORM}	Maximum repetitive peak voltage per DIN V VDE V 0884-10		566	V_{PK}
V_{PR}	Input-to-output test voltage per DIN V VDE V 0884-10	After Input/Output safety test subgroup 2/3, V_{PR} = V_{IORM} x 1.2, t = 10 s, Partial discharge < 5 pC	680	V_{PK}
		Method a, After environmental tests subgroup 1, V_{PR} = V_{IORM} x 1.6, t = 10 s, Partial Discharge < 5 pC	906	
		Method b1, V_{PR} = V_{IORM} x 1.875, t = 1 s (100% Production test) Partial discharge < 5 pC	1062	
V_{IOTM}	Maximum transient overvoltage per DIN V VDE V 0884-10	V_{TEST} = V_{IOTM} t = 60 sec (qualification) t= 1 sec (100% production)	4242	V_{PK}
V_{IOSM}	Maximum surge isolation voltage per DIN V VDE V 0884-10	Test method per IEC 60065, 1.2/50 µs waveform, V_{TEST} = 1.3 x V_{IOSM} = 7800 V_{PK} (qualification)	6000	V_{PK}
V_{ISO}	Withstand isolation voltage per UL 1577	V_{TEST} = V_{ISO} = 3000 V_{RMS}, t = 60 sec (qualification); V_{TEST} = 1.2 x V_{ISO} = 3600 V_{RMS}, t = 1 sec (100% production)	3000	V_{RMS}
R_S	Insulation resistance	V_{IO} = 500 V at T_S = 150°C	>10^9	Ω
	Pollution degree		2	

(1) Climatic Classification 40/125/21

Table 1. IEC 60664-1 Ratings Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	II
Installation classification	Rated mains voltage ≤ 150 V_{RMS}	I–IV
	Rated mains voltage ≤ 300 V_{RMS}	I–III

8.3.1.3 Regulatory Information

VDE	CSA	UL	CQC
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 61010-1 (VDE 0411-1):2011-07	Approved under CSA Component Acceptance Notice 5A, IEC 60950-1, and IEC 61010-1	Recognized under UL 1577 Component Recognition Program	Certified according to GB4943.1-2011
Basic Insulation Maximum Transient Overvoltage, 4242 V_{PK}; Maximum Surge Isolation Voltage, 6000 V_{PK}; Maximum Repetitive Peak Voltage, 566 V_{PK}	400 V_{RMS} Basic Insulation and 200 V_{RMS} Reinforced Insulation working voltage per CSA 60950-1-07+A1+A2 and IEC 60950-1 2nd Ed.+A1+A2; 300 V_{RMS} Basic Insulation working voltage per CSA 61010-1-12 and IEC 61010-1 3rd Ed.	Single protection, 3000 V_{RMS} (1)	Basic Insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V_{RMS} maximum working voltage
Certificate number: 40016131	Master contract number: 220991	File number: E181974	Certificate number: CQC15001121656

(1) Production tested ≥ 3600 V_{RMS} for 1 second in accordance with UL 1577.

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8.3.1.4 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S	Safety input, output, or supply current	$R_{\theta JA}$ = 119.9 °C/W, V_I = 5.5 V, T_J = 150°C, T_A = 25°C			190	mA
		$R_{\theta JA}$ = 119.9 °C/W, V_I = 3.6 V, T_J = 150°C, T_A = 25°C			290	
T_S	Maximum case temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the *Absolut Maximun Ratings* table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Information* table is that of a device installed on a High-K Test Board for Leaded Surface-Mount Packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

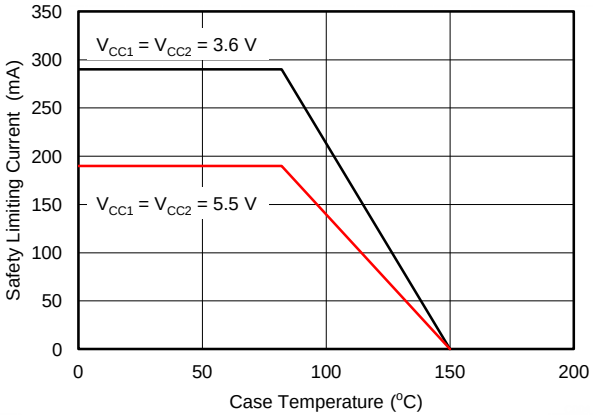

Figure 13. θ_{JC} Thermal Derating Curve per DIN V VDE 0884-10

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8.4 Device Functional Modes

Table 2. Function Table(1)

V_{CC1}	V_{CC2}	IN	OUT	
			ISO7310C	ISO7310FC
PU	PU	H	H	H
		L	L	L
		Open	H(2)	L(3)
PD	PU	X	H(2)	L(3)
X	PD	X	Undetermined	Undetermined

(1) PU = Powered up (V_{CC} ≥ 3 V); PD = Powered down (V_{CC} ≤ 2.1 V); X = Irrelevant; H = High level; L = Low level
(2) In fail-safe condition, output defaults to high level
(3) In fail-safe condition, output defaults to low level

8.4.1 Device I/O Schematics

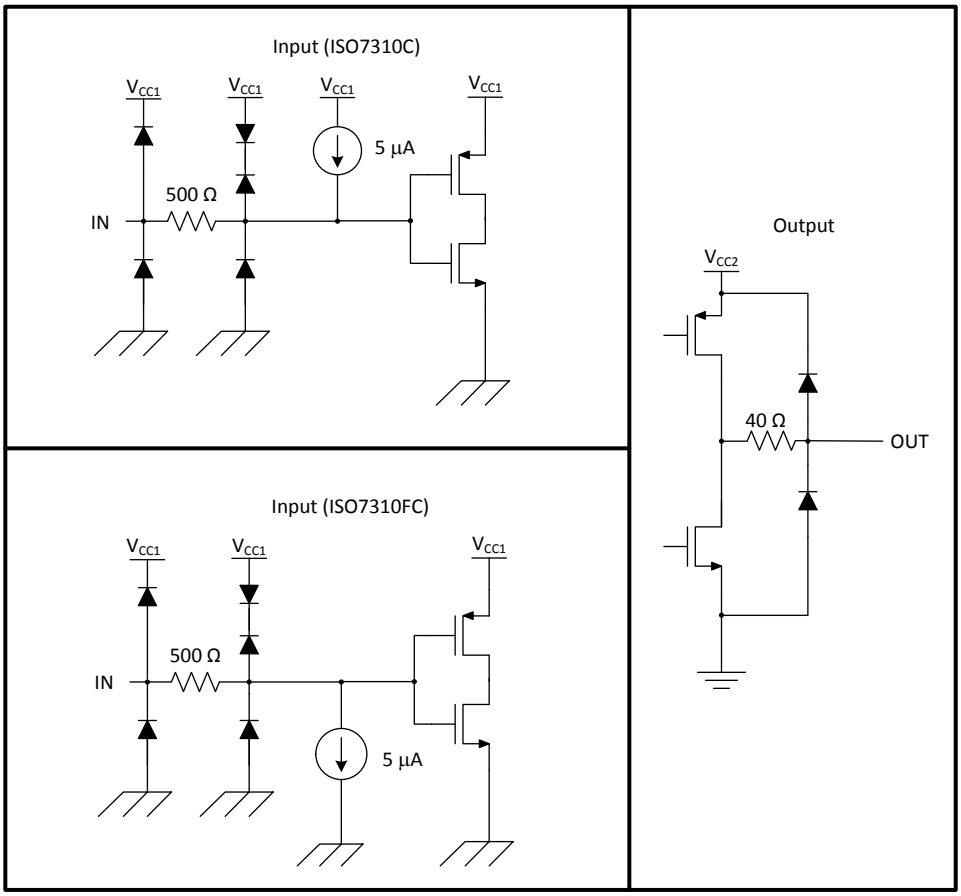

Figure 14. Device I/O Schematics

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9 Applications and Implementation

NOTE

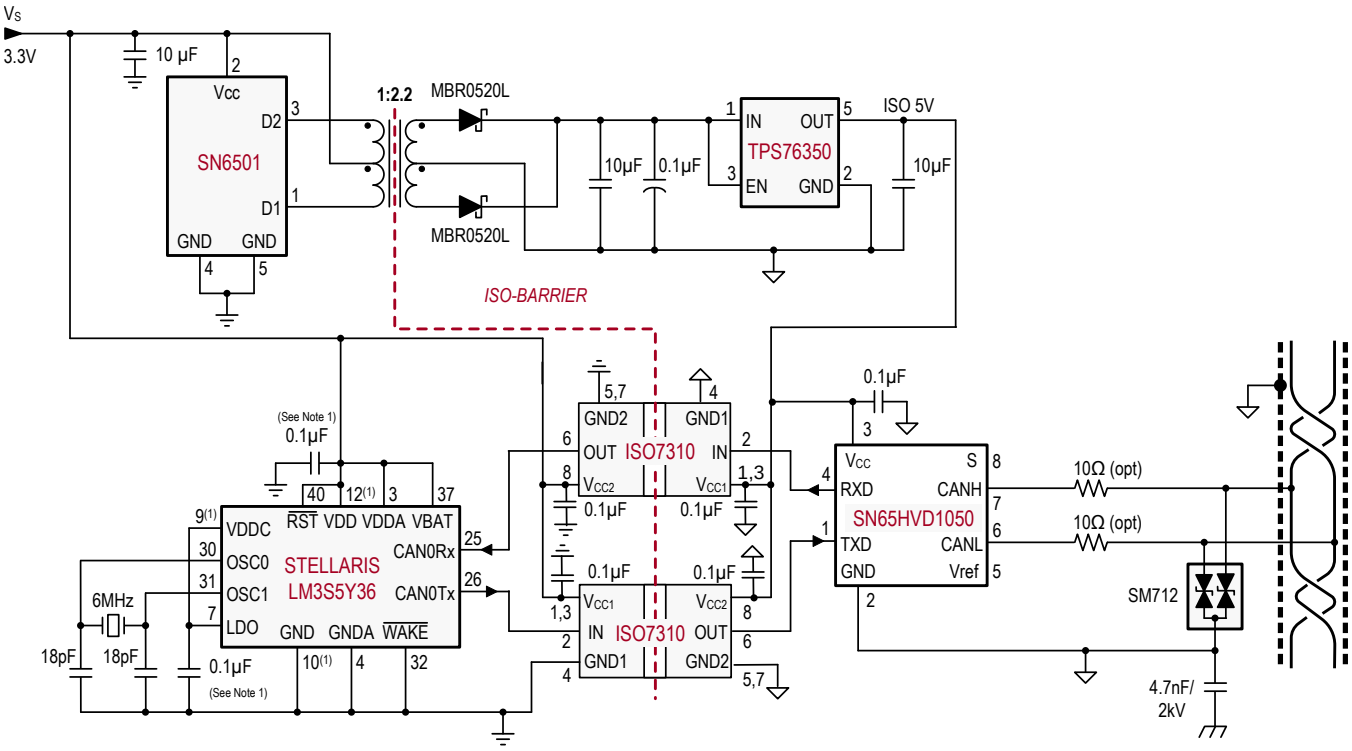
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

ISO7310x use single-ended TTL-logic switching technology. The supply voltage range is from 3 V to 5.5 V for both supplies, V_{CC1} and V_{CC2}. When designing with digital isolators, it is important to keep in mind that due to the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (i.e. µC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

ISO7310 can be used with Texas Instruments' microcontroller, CAN transceiver, transformer driver, and low-dropout voltage regulator to create an Isolated CAN Interface as shown in Figure 15.



(1) Multiple pins and capacitors omitted for clarity purpose.

Figure 15. Isolated CAN Interface

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Typical Application (continued)

9.2.1 Design Requirements

9.2.1.1 Typical Supply Current Equations

At $V_{CC1} = V_{CC2} = 5$ V

- $I_{CC1} = 0.30517 + (0.01983 \times f)$
- $I_{CC2} = 1.40021 + (0.02879 \times f) + (0.0021 \times f \times C_L)$

At $V_{CC1} = V_{CC2} = 3.3$ V

- $I_{CC1} = 0.18133 + (0.01166 \times f)$
- $I_{CC2} = 1.053 + (0.01607 \times f) + (0.001488 \times f \times C_L)$

I_{CC1} and I_{CC2} are typical supply currents measured in mA, f is data rate measured in Mbps, C_L is the capacitive load measured in pF.

9.2.2 Detailed Design Procedure

Unlike optocouplers, which need external components to improve performance, provide bias, or limit current, ISO7310x only need two external bypass capacitors to operate.

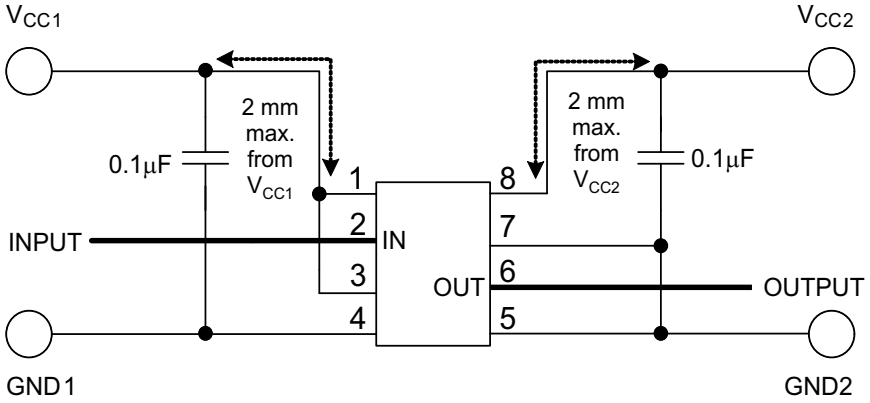

Figure 16. Typical ISO7310 Circuit Hook-up

9.2.2.1 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO7310x incorporate many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

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Typical Application (continued)

9.2.3 Application Performance Curves

Typical eye diagrams of ISO7310x below indicate very low jitter and wide open eye at the maximum data rate of 25 Mbps.

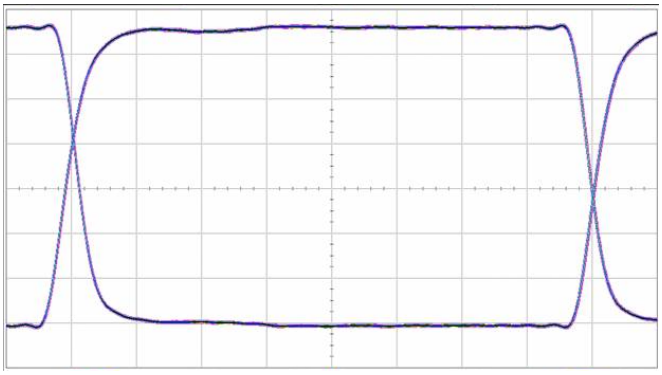

Figure 17. Eye Diagram at 25 Mbps, 5V and 25°C

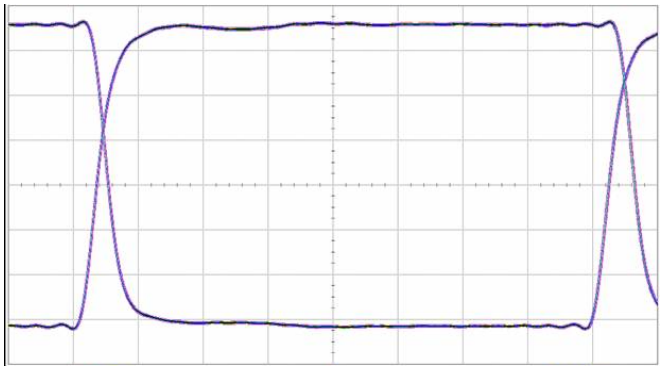

Figure 18. Eye Diagram at 25 Mbps, 3.3V and 25°C

10 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, a 0.1 µF bypass capacitor is recommended at input and output supply pins (V_{CC1} & V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' SN6501. For such applications, detailed power supply design and transformer selection recommendations are available in SN6501 datasheet (SLLSEA0) .

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11 Layout

11.1 PCB Material

For digital circuit boards operating below 150 Mbps, (or rise and fall times higher than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 epoxy-glass as PCB material. FR-4 (Flame Retardant 4) meets the requirements of Underwriters Laboratories UL94-V0, and is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and its self-extinguishing flammability-characteristics.

11.2 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see Figure 19). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100pF/in^2.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power / ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see Application Note SLLA284, *Digital Isolator Design Guide*.

11.3 Layout Example

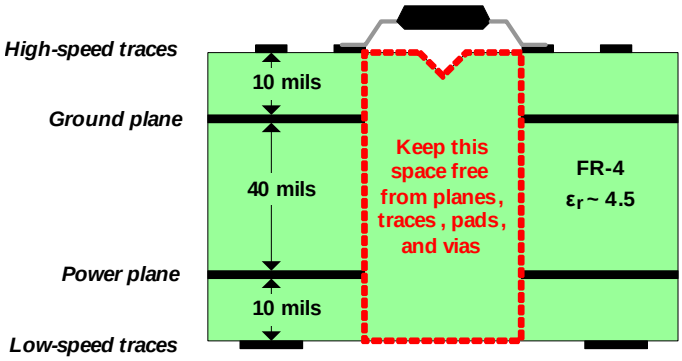

Figure 19. Recommended Layer Stack

12 器件和文档支持

12.1 商标

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12.2 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.3 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、首字母缩略词和定义。

《隔离相关术语》，SLLA353

13 机械、封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISO7310CD	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310C
ISO7310CD.A	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310C
ISO7310CD.B	Active	Production	SOIC (D) | 8	75 | TUBE	-	Call TI	Call TI	-40 to 125	
ISO7310CDR	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310C
ISO7310CDR.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310C
ISO7310CDR.B	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	-	Call TI	Call TI	-40 to 125	
ISO7310FCD	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310FC
ISO7310FCD.A	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310FC
ISO7310FCD.B	Active	Production	SOIC (D) | 8	75 | TUBE	-	Call TI	Call TI	-40 to 125	
ISO7310FCDR	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310FC
ISO7310FCDR.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7310FC
ISO7310FCDR.B	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	-	Call TI	Call TI	-40 to 125	

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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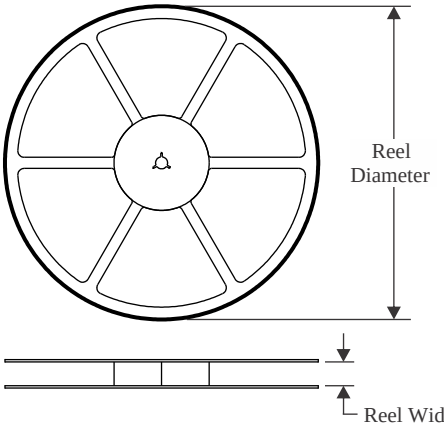
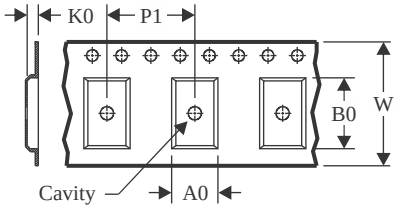
TAPE AND REEL INFORMATION

REEL DIMENSIONS

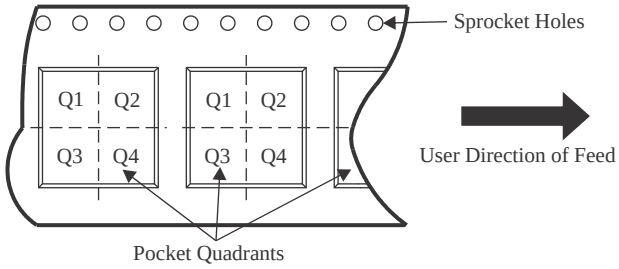


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

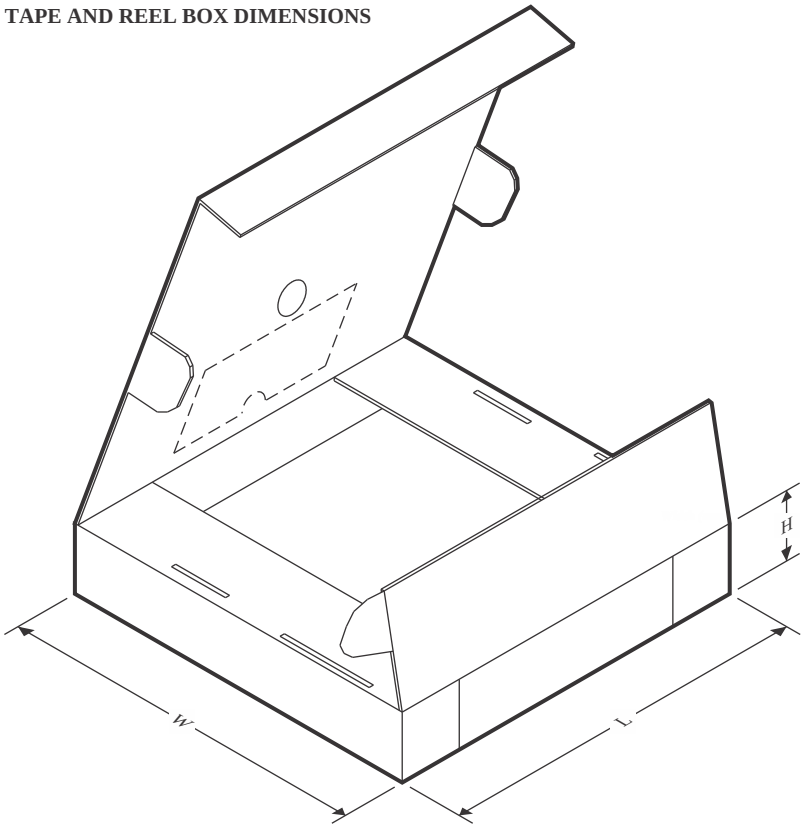
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7310CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7310FCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

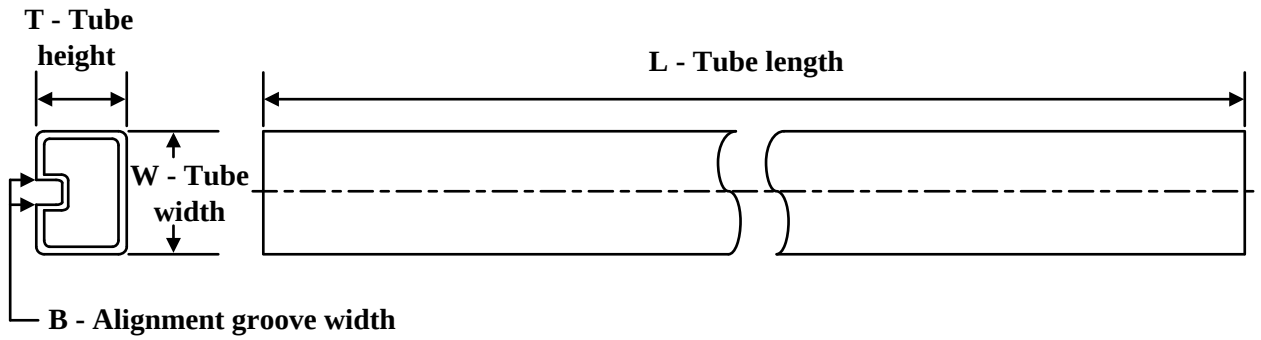
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7310CDR	SOIC	D	8	2500	350.0	350.0	43.0
ISO7310FCDR	SOIC	D	8	2500	350.0	350.0	43.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
ISO7310CD	D	SOIC	8	75	505.46	6.76	3810	4
ISO7310CD.A	D	SOIC	8	75	505.46	6.76	3810	4
ISO7310FCD	D	SOIC	8	75	505.46	6.76	3810	4
ISO7310FCD.A	D	SOIC	8	75	505.46	6.76	3810	4

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